12 V High-Side Hot-Swap Hall-Effect-Based Current Monitor IC

Discontinued Product

These parts are no longer in production The device should not be purchased for new design applications. Samples are no longer available.

Date of status change: July 14, 2022

Recommended Substitutions:

For existing customer transition, and for new customers or new applications, use ACS726.

NOTE: For detailed information on purchasing options, contact your local Allegro field applications engineer or sales representative.

12 V High-Side Hot-Swap Hall-Effect-Based Current Monitor IC

FEATURES AND BENEFITS

- Hall-effect current monitor—no external sense resistor required
- Analog output voltage (factory trimmed for gain and offset) proportional to applied current
- External high-side FET gate drive
- 240V*A Power Fault Protection with user-programmable delay
- User programmable Overcurrent Fault Protection with programmable delay
- 1.5 mΩ internal conductor resistance
- Short Circuit Protection isolates failed supply from output in < 2 µs
- Active low Fault indicator output signal
- External FET failure detection with active low S1 Short failure indicator output signal
- User controlled soft start / hot-swap function
- Logic enable input pin
- 10.8 to 13.2 V, single-supply operation
- 2 kV ESD protection for all pins

PACKAGE: 24-pin QSOP (suffix LF)
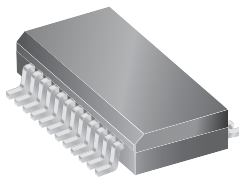
Approximate Footprint

DESCRIPTION

The ACS760 combines Allegro™ Hall-effect current sense technology with a hot-swap controller resulting in a more efficient integrated controller for 12 V applications. By eliminating the need for a shunt resistor, the I^2R losses in the power path are reduced.

When the ACS760 is externally enabled, and the voltage rail is above the internal UVLO threshold, the internal charge pump drives the gate of the external FET. When a fault is detected, the gate is disabled while simultaneously alerting the application that a fault has occurred.

The integrated protection in the ACS760 incorporates three levels of fault protection, which includes a Power Fault with user-programmable delay, a user-programmable Overcurrent Fault threshold with programmable delay, and Short Circuit protection, which disables the gate in less then 2 µs.

Additionally, in the event the external high-side FET fails short, the ACS760 detects the S1 Short failure and immediately disables the gate and alerts the host system. Unlike the three protection faults, cycling the EN pin does not reset the S1 Short failure. Power to the device must be cycled.

Typical Application
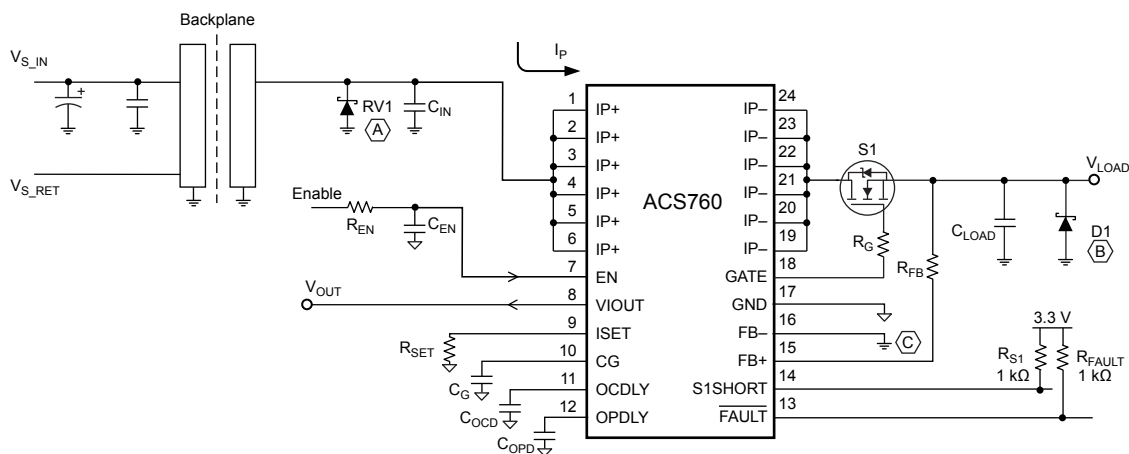
(A) RV1 is required only for inductive loads.
(B) D1 should be a Schottky for inductive loads, to eliminate over-stress of the ACS760.
(C) FB– is tied to GND at the point of load.

Selection Guide

Part Number	Package	Packing*
ACS760ELFTR-20B-T	QSOP24 surface mount	2500 pieces/reel

*Contact Allegro for additional packing options

Absolute Maximum Ratings

Characteristic	Symbol	Notes	Rating	Units
Forward Voltage, IP*x* pins*	V_{CC}		24	V
GATE Drive Output Voltage*	V_{GATE}		32	V
FB+ Forward Voltage*	V_{FB+}		24	V
EN Forward Voltage*	V_{EN}		32	V
All Other Pins Forward Voltage	V_{IN}		8	V
Reverse DC Voltage, All Pins*	V_R		−0.5	V
Reverse Transient DC Voltage, All Pins*	V_r	10 µs pulse	−5	V
Current Level Output Current Source	$I_{VIOUT(Source)}$		1	mA
Current Level Output Current Sink	$I_{VIOUT(Sink)}$		1	mA
Operating Ambient Temperature	T_A	Range E	−40 to 85	°C
Maximum Junction Temperature	$T_J(max)$		165	°C
Storage Temperature	T_{stg}		−65 to 170	°C

* With respect to GND.

Pinout Diagram

IP+	1	24 IP−
IP+	2	23 IP−
IP+	3	22 IP−
IP+	4	21 IP−
IP+	5	20 IP−
IP+	6	19 IP−
EN	7	18 GATE
VIOUT	8	17 GND
ISET	9	16 FB−
CG	10	15 FB+
OCDLY	11	14 S1SHORT
OPDLY	12	13 $\overline{\text{FAULT}}$
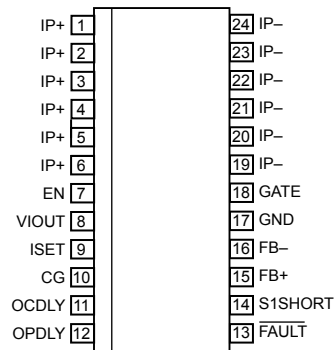
Terminal List Table

Number	Name	Function
1-6	IP+	Primary sampled current conduction path input; power input pins: connected to V_{CC}
7	EN	Enable pin. Toggling this pin to the low state after a FAULT condition resets the ACS760.
8	VIOUT	Analog current level output. Output voltage on this pin is proportional to the current flowing from the IP+ pins to the IP− pins.
9	ISET	Terminal for R_{SET} resistor. Sets Fault Current Threshold, I_{PF}, via external resistor, R_{SET}, connected between this terminal and GND. Factory trimmed 100 µA current source flows out of this pin.
10	CG	Terminal for C_G capacitor. May be used to adjust the turn-on time and soft start control of an external MOSFET, S1. Voltage on this pin limits inrush current through MOSFET S1. Set via external capacitance, C_G, connected between this pin and GND. This capacitor is charged by an internal 20 µA current source.
11	OCDLY	Terminal for external capacitor, C_{OCD}, Used to adjust delay for overcurrent shutdown, set via the external capacitor, C_{OCD}, connected between this pin and GND.
12	OPDLY	Terminal for external capacitor, C_{OPD}, Used to adjust delay for overpower shutdown, set via the external capacitor, C_{OPD}, connected between this pin and GND.
13	$\overline{\text{FAULT}}$	Active low; output signal for short circuit and 240 V*A overload faults; does not trip for S1 short circuit fault. Connect a 1 kΩ pull-up resistor between this pin and the 3.3 V rail.
14	S1SHORT	Active low; output signal for MOSFET S1 failure. Connect a 1 kΩ pull-up resistor between this pin and the 3.3 V rail.
15	FB+	Input of positive feedback on output voltage. Used to determine 240 V*A threshold by difference between FB+ and FB− pins.
16	FB-	Input of negative feedback on output voltage. Used to determine 240 V*A threshold by difference between FB+ and FB− pins. Pulling the FB− pin to 3.3 V, and the OPDLY pin to GND, disables the 240 V*A power fault, which allows the ACS760 to operate purely in Current Mode.
17	GND	Terminal for ground connection.
18	GATE	Terminal for external MOSFET, S1. Provides output voltage to drive S1. Current through S1 is controlled at start-up by external capacitance connected between the CG pin and GND.
19-24	IP−	Primary sampled current conduction path output; power output pins.

Functional Block Diagram
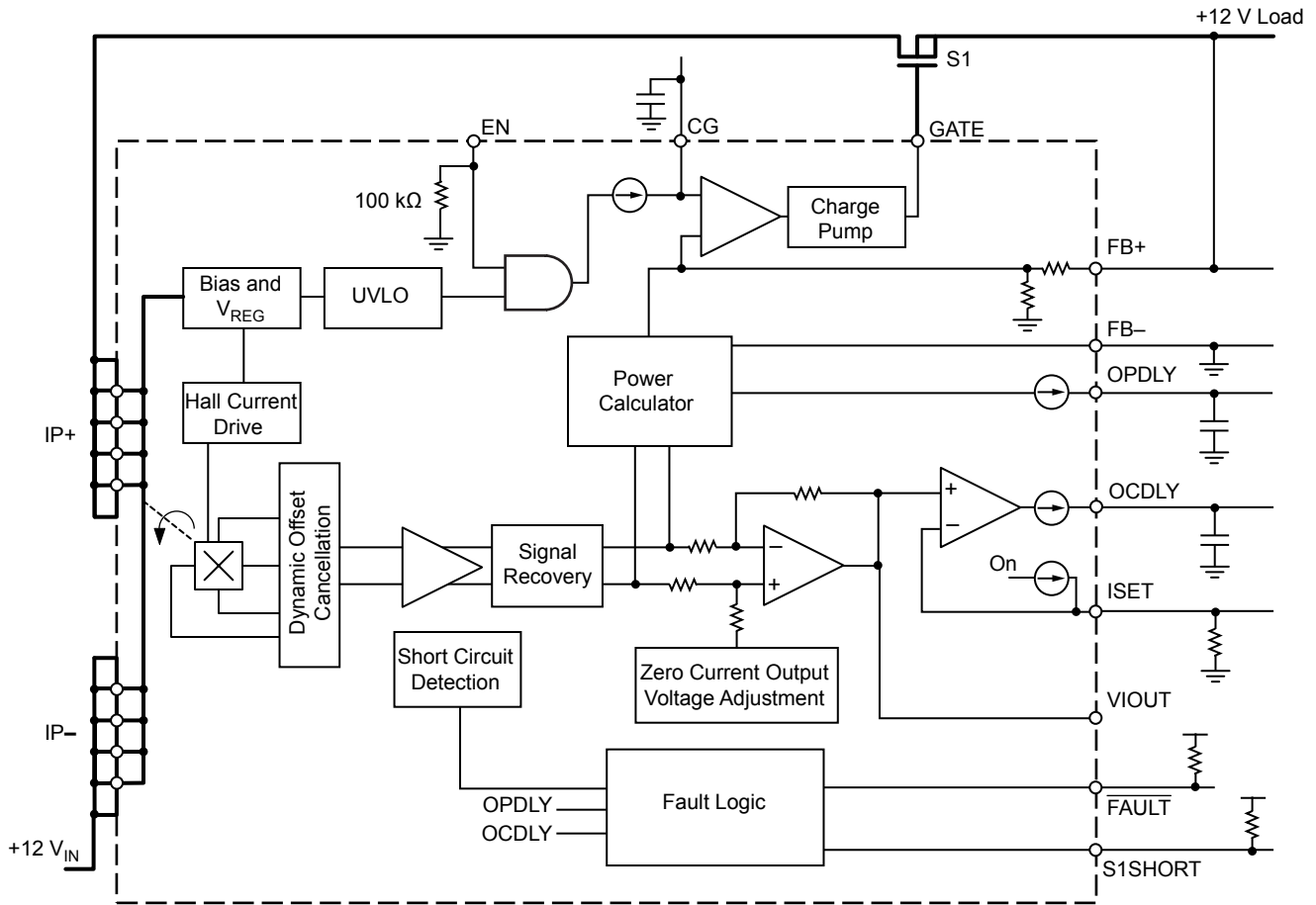
OPERATING CHARACTERISTICS valid at V_{CC} = 12 V, T_A = 0°C to 85°C, unless otherwise noted

Characteristic	Symbol	Test Conditions	Min.	Typ.	Max.	Units
GENERAL ELECTRICAL CHARACTERISTICS						
Linear Sensing Range	I_P	Current flows from IP+ to IP- pins	0	–	55	A
Primary Conductor Resistance	$R_{PRIMARY}$	T_A = 25°C	–	1.5	–	mΩ
Supply Voltage	V_{CC}	Voltage applied to IP+ pins	–	12	–	V
Supply Current	I_{CC}		–	10	12	mA
Undervoltage Lockout (UVLO)	V_{UVLOH}	V_{CC} rising and CG pin current source turns on, EN pin = high	–	–	10.5	V
	V_{UVLOL}	V_{CC} falling and CG pin current source turns off, EN pin = high	7.1	–	–	V
UVLO Delay to Chip Enable/ Disable	t_{UVLOE}	Enabling, measured from rising $V_{CC} > V_{UVLOH}$ to $V_{GATE} > 1$ V	–	500	900	µs
	t_{UVLOD}	Disabling, from falling $V_{CC} < V_{UVLOL}$ to $V_{GATE} < 1$ V	–	–	2	µs
FB+ to FB– Input Resistance	R_{FB}	T_A = 25°C	–	240	–	kΩ
CURRENT SENSE PERFORMANCE CHARACTERISTICS						
VIOUT Analog Output Propagation Time	t_{PROP}	T_A = 25°C, I_P = 0 →20 A, capacitance from VIOUT to GND = 100 pF	–	2	–	µs
VIOUT Analog Output 10-90% Rise Time	t_r	T_A = 25°C, I_P = 0 →20 A, capacitance from VIOUT to GND = 100 pF	–	5	–	µs
VIOUT Analog Signal Bandwidth[1]	f_{3dB}	–3 dB, Ip = 10 A peak-to-peak, T_A = 25°C, no external device filter, capacitance from VIOUT to GND = 100 pF	–	50	–	kHz
VIOUT Analog Signal Sensitivity	Sens	T_A = 25°C	–	65	–	mV/A
		Over full ambient operating temperature range	61.5	–	67.5	mV/A
		T_A = 25°C	–	5.416	–	mV/G
		Over full ambient operating temperature range	5.275	–	5.558	mV/G
Sensitivity Slope Over Temperature	$\Delta Sens_{TA}$	T_A = 0°C to 25°C	–	0.042	–	mV/A/°C
		T_A = 25°C to 85°C	–	0.027	–	mV/A/°C
VIOUT Analog Noise Level	$V_{NOISE(PP)}$	Mean peak-to-peak, T_A = 25°C, 50 kHz external device filter	–	20	–	mV
VIOUT Analog Nonlinearity	E_{LIN}	Over full ambient operating temperature range and linear sensing range	–	±0.5	±2.0	%
Zero Current Output Voltage	$V_{IOUT(Q)}$	T_A = 0°C to 55°C	0.38	–	0.42	V
		T_A = 0°C to 85°C	0.37	0.4	0.43	V
Zero Current Output Slope Over Temperature	$\Delta I_{OUT(Q)TA}$	T_A = 0°C to 25°C	–	–0.148	–	mV/°C
		T_A = 25°C to 85°C	–	–0.057	–	mV/°C
Output Voltage Saturation Limits[2]	V_{OL}	T_A = 25°C	–	0.25	–	V
	V_{OH}	T_A = 25°C	–	3.6	–	V
VIOUT Total Error % of I_P	E_{TOT}	T_A = 25°C, I_P = 20 A	–	±1.0	–	%
		T_A = 0°C to 85°C, I_P = 20 A	–	–	±3.5	%
VIOUT DC Output Resistance	R_{VIOUT}	I_{VIOUT} = 1 mA	–	1	–	Ω
CURRENT FAULT PERFORMANCE CHARACTERISTICS						
Load Power Fault Threshold	$P_{F(th)}$		222	230	238	W
240 V*A Fault Signal Delay	t_{PFH}	T_A = 25°C, measured from FAULT signal to $V_{GATE} < 1$ V, 2.2 µF capacitance from OPDLY pin to GND, load step from 17 A to 23 A in 100 ns	–	425	–	ms
	t_{PFL}	T_A = 25°C, measured from FAULT signal to $V_{GATE} < 1$ V, OPDLY pin open, load step from 17 A to 23 A in 100 ns	–	10	12	µs
240 V*A Fault Signal Delay Drift	Δt_{PF}	Over full operating ambient temperature range, external capacitor with ±5% tolerance	–15	–	15	%
Internal –3 dB Filter Frequency for FB+ and FB– Pins	f_{FBFILT}	T_A = 25°C	–	50	–	kHz

Continued on the next page…

OPERATING CHARACTERISTICS, (continued) Valid at V_{CC} = 12 V, T_A = 0°C to 85°C, unless otherwise noted

Characteristic	Symbol	Test Conditions	Min.	Typ.	Max.	Units
I_P Fault Switchpoint Tolerance[3]	E_{PF}	Percentage error of I_{PF}	–15	–	15	%
I_{PF} Fault Signal Delay[4]	$t_{IPFLmax}$	Measured from FAULT signal to V_{GATE} < 1 V, OCDLY pin open, load step from 17 A to 45 A in 100 ns	–	8	12	µs
	t_{IPFH}	Measured from FAULT signal to V_{GATE} < 1 V, 2.2 nF capacitance from OCDLY pin to GND, load step from 17 A to 45 A in 100 ns	–	425	–	µs
Maximum Short Circuit/Overcurrent Fault Threshold[5]	I_{SC}		60	110	160	A
Short Circuit/Overcurrent Fault Gate Delay	t_{SC}	Measured from FAULT signal to V_{GATE} < 1 V, Includes t_{GF}	–	2	3	µs
VOLTAGE FAULT PERFORMANCE CHARACTERISTICS						
Internal Pull-Down Resistance Between EN and GND	R_{EN}	T_A = 25°C	–	100	–	kΩ
EN Voltage Threshold[6]	V_{ENH}	IC enabled when V_{EN} > V_{ENH}	1.93	–	–	V
	V_{ENL}	IC disabled when V_{EN} < V_{ENL}	–	–	1	V
S1 Short Circuit Detection Current[7]	I_{S1S}	IC enabled or disabled	0.9	1.5	2.1	A
S1 Short Circuit Detection Delay	t_{S1S}	Measured from disablement of the device to detection of an S1 fault	–	–	45	µs
S1SHORT Output Voltage	V_{S1SOL}	$I_{S1SHORT}$ = 3 mA sink current	–	–	0.4	V
S1SHORT Output Leakage Current	I_{S1SIH}	$V_{S1SHORT}$ = 3.3 V	–	–	5	µA
FAULT Output Voltage	$V_{FAULTOL}$	I_{FAULT} = 3 mA sink current	–	–	0.4	V
FAULT Output Leakage Current	$I_{FAULTIH}$	V_{FAULT} = 3.3 V	–	–	5	µA
GATE DRIVE PERFORMANCE CHARACTERISTICS						
Internal Charge Pump Voltage	V_{CP}	T_A = 25°C	–	V_{CC}+10	–	V
Average GATE Drive Current	I_{GD}	V_{CC} = 12 V, T_A = 25°C	25	50	–	µA
Charge Pump Switching Frequency	f_{CP}	T_A = 25°C	–	1	–	MHz
GATE Rise Time	t_{GR}	T_A = 25°C, external MOSFET S1 gate capacitance = 5.8 nF, measured from V_{GATE} = 0 V to 15 V, CG pin open, no output load capacitance	–	1	–	ms
		T_A = 25°C, external MOSFET S1 gate capacitance = 5.8 nF, measured from V_{GATE} = 0 V to 15 V, 3.75 µF capacitor connected between CG and GND pins	–	500	–	ms
GATE Sink Resistance	R_{Gsink}		–	20	30	Ω
GATE Discharge Current	I_{GD}	V_{GATE} = V_{CC} + 10 V	–	1000	–	mA
GATE Shutdown Delay	t_{GSD}	Measured from fault event to start of GATE pull down	–	200	–	ns
GATE Maximum Fall Time	t_{GF}	Measured from V_{GATE} = 90% of maximum to V_{GATE} < 1 V, external MOSFET S1 gate capacitance = 5.8 nF. EN pin switched from high to low, FAULT or S1SHORT signal	–	800	–	ns
CG Output Current	I_{SLEW}	T_A = 25°C	18	20	22	µA

[1]The small signal, AC bandwidth of this device is approximately 90 kHz.

[2]This test requires currents sufficient to swing the output driver between the fully off state and the saturated state. Assumes that the VIOUT pin is connected to an analog-to-digital converter that saturates at 2.5 V. The VIOUT signal is linear above 2.5 V, however, this test is NOT intended to indicate a range of linear operation.

[3]Assumes that a 1% resistor with a flat temperature coefficient is connected between the ISET and GND pins.

[4]Can exceed t_{IPFH}(max) delay period via the use of a larger external capacitor. Voltage trip point on the high side of the capacitor is 3.85 V.

[5]This parameter is internally programmed and cannot be controlled by the end user.

[6]The FAULT output signal is latched. After a latched fault event, the device will be reset only when either: (a) V_{EN} drops below V_{ENL}, or (b) the power to the device (applied to the IP+ pins) is toggled off and then back on.

[7]The voltage on the gate of the external MOSFET S1 does not need to be < 1 V in order for the device to detect an S1 short circuit condition. The device does detect a faulty S1 when the gate of S1 is shorted to the S1 source or drain terminal.

Soft Start and Fault Characteristics

Gate turn on rise time, t_{GR}. Set by external capacitance, C_G, on the CG pin, such that $C_G = 7.5 \times t_{GR}$, where C_G is in µF and t_{GR} is rise time in seconds. For example, a 3.9 µF capacitor connected from the CG pin to GND (without an output load) will yield a rise time of approximately 500 ms: $C_G \cong 7.5 \times 0.5\ s = 3.75\ \mu F$, $\cong 3.9\ \mu F$ (a common capacitor value).

When the CG pin is kept open, the ACS760 has a minimum t_{GR} of 1 ms typical.

I_{PF} fault signal delay, t_{IPF}. This is the delay from high current level fault sense to the start of turn-off of the external MOSFET S1 turn-off. Set by external capacitance, C_{OCD}, on the OCDLY pin, such that $C_{OCD} = 5.17 \times t_{rOCD}$; where C_{OCD} is in µF and t_{rOCD} is rise time in seconds.

When the OCDLY pin is kept open, the IC has a minimum fault delay, $t_{IPFLmax}$, of 8 µs maximum.

Load power fault signal delay, t_{PFL}. This is the delay from maximum power level fault, $P_{F(th)}$, sense to the start of external MOSFET S1 turn-off. Set by external capacitance, C_{OPD}, on the OPDLY pin, such that $C_{OPD} = 5.17 \times t_{rOPD}$; where C_{OPD} is in µF and t_{rOPD} is rise time in seconds.

The IC has a minimum fault delay when the OPDLY pin kept open of 10 µs typical.

I_{PF} fault current setting, I_{PF}. The I_{PF} upper trip level may be set by using a resistor between the ISET pin and GND, such that $R_{SET} = 10^4\ (0.4 + 0.065 \times I_{PF})$, where I_{PF} is in A and R_{SET} in Ω.

Accuracy Characteristics

Sensitivity, Sens. The change in device output in response to a 1 A change through the primary conductor. Sens is the product of the magnetic circuit sensitivity (G/A) and the linear IC amplifier gain (mV/G). The linear IC amplifier gain is trimmed at Allegro final test to optimize the sensitivity (mV/A) for the full-scale current range of the device.

Noise, $V_{NOISE(PP)}$. The product of the linear IC amplifier gain (mV/G) and the noise floor for the Allegro Hall effect linear IC. Dividing the noise (mV) by the sensitivity (mV/A) provides the smallest current that the device is able to resolve.

Nonlinearity, E_{LIN}. The linearity of the V_{IOUT} signal is the degree to which the voltage output from the device varies in direct proportion to the primary sensed current, up to 20 A. Nonlinearity reveals the maximum deviation in the slope of the device transfer function compared to the slope of the ideal transfer curve for this transducer. The following equation is used to derive the linearity:

$$100 \left\{ 1 - \left[\frac{(V_{IOUT\_full\text{-}scale\ amperes} - V_{IOUT(Q)})}{2\ (V_{IOUT\_half\text{-}scale\ amperes} - V_{IOUT(Q)})} \right] \right\},$$

where full-scale current is 20 A, and half-scale current is 10 A.

Zero Current Output Voltage, $V_{IOUT(Q)}$. The output of the device when the primary current, I_P, is 0 A. Variation in $V_{IOUT(Q)}$ can be attributed to the resolution of the Allegro linear IC quiescent voltage trim and thermal drift.

V_{IOUT} Total Error, E_{TOT}. The maximum percentage deviation of the actual output from its ideal value, based on an ideal sensitivity of 65.7 mV/A at 25°C and 64.3 mV/A at 85°C.

Dynamic Response Characteristics

Propagation delay, t_{PROP}. The time required for the device output to reflect a change in the primary current signal. Propagation delay is attributed to inductive loading within the linear IC package, as well as in the inductive loop formed by the primary conductor geometry. Propagation delay can be considered as a fixed time offset and may be compensated.
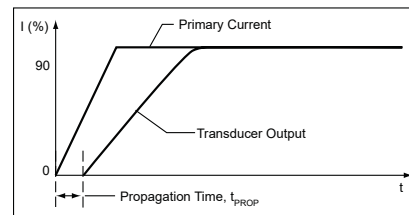
Response time, $t_{RESPONSE}$. The time interval between a) when the primary current signal reaches 90% of its final value, and b) when the device reaches 90% of its output corresponding to the applied current.
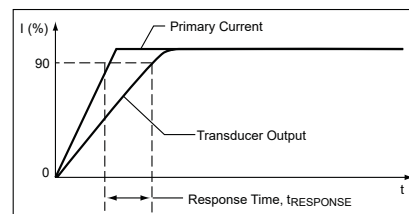
Rise time (t_r). The time interval between a) when the device reaches 10% of its full-scale value, and b) when it reaches 90% of its full scale value. The rise time to a step response is used to derive the bandwidth of the device, in which $f(–3\ dB) = 0.35 / t_r$. Both t_r and $t_{RESPONSE}$ are detrimentally affected by eddy current losses observed in the conductive IC ground plane.

7
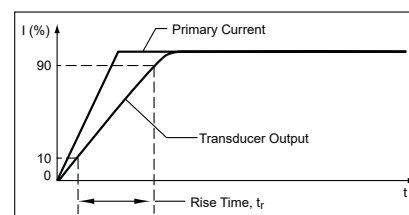
240 V*A Fault Operation

The timing diagram in figure 1 shows characteristic operation of the ACS760 when the power consumed from the 12 V system bus exceeds a 240 V*A or 240 W level. The system power supply bus reaches the nominal steady state level of 12 V before the EN pin (Enable pin, active high) of the ACS760 transitions to the high state at time t_{EN1}. Note that, when the EN pin is in the low state, the GATE pin is actively pulled low. However, as shown in the timing diagram, the voltage on the GATE pin increases with a positive slope after the EN pin transitions to the high state. The ramp rate of the GATE pin is controlled by the value of the capacitor connected to the CG pin.

At a certain GATE voltage, current begins to flow through the external protection MOSFET, S1, and this current increases as the GATE voltage increases. The voltage at the VIOUT pin, which is the current device output voltage of the ACS760, proportionally tracks the current that flows through the MOSFET.

In the timing diagram, the system is in normal, steady state operation up until the time t_{INIT_F}. At t_{INIT_F}, the current load on the 12 V power supply increases from 19.2 to 22 A and the ACS760 internally registers a 240 V*A fault condition. At this time, the

voltage on the OPDLY pin increases with a constant slope. (This slope is controlled by the value of the capacitor connected to the OPDLY pin). This voltage continues to increase with a constant slope until either:

- The OPDLY pin voltage reaches a threshold of 3.85 V (if this occurs, the FAULT signal is latched in the low state), or

- The power consumption of the system falls below 240 V*A (at which time the OPDLY pin voltage is pulled to ground)

A 240 V*A fault event is detected at t_{240VA_F}. At this time, the FAULT signal transitions to the low state and the GATE pin is pulled to ground. The FAULT signal is latched and the chip will pull down the GATE voltage until the EN pin of the ACS760 transitions to the low state and then back to the high state. As shown in the timing diagram, certain ACS760 signals (the FAULT signal and the OPDLY pin voltage) are reset when the EN pin transitions to the low state. These signals are reset in order to guarantee normal device operation (soft start and fault monitoring) when the EN signal transitions back to the high state.
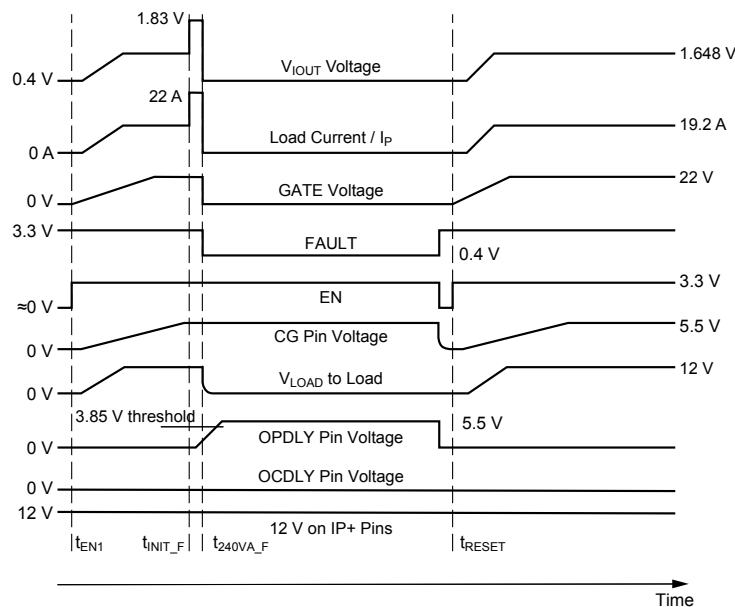

Figure 1. Timing Diagram for 240 V*A Fault

Soft Short Circuit Fault Operation

The timing diagram in figure 2 shows the characteristic operation of the ACS760 when the current load on the 12 V system bus jumps from the 19 to 20 A level to the 40 A level. The 40 A load is typically indicative of a soft short circuit on the I_{LOAD} side of the external MOSFET.

In figure 2, the system power supply bus reaches the nominal steady state level of 12 V before the EN pin (Enable pin, active high) of the ACS760 transitions to the high state at time t_{EN1}. Note that when the EN pin is in the low state, the GATE pin is actively pulled low. However, as shown in the timing diagram, the voltage on the GATE pin increases with a positive slope after the EN pin transitions to the high state. The ramp rate of the GATE pin is controlled by the value of the capacitor connected to the CG pin.

At a certain GATE voltage, current begins to flow through the external protection MOSFET, S1, and this current increases as the GATE voltage increases. The voltage at the VIOUT pin, which is the current device output voltage of the ACS760, proportionally tracks the current that flows through the MOSFET.

In the timing diagram the system is in normal, steady state operation up until the time t_{INIT_F}. At t_{INIT_F} the current load on the 12 V power supply increases from 19.2 A to 40 A and the ACS760 internally registers both a 240 V*A fault condition and an I_{PF} fault condition. In this example, the I_{SET} voltage was set at 3.0 V, which corresponds to a 40 A fault threshold. At t_{INIT_F},

the voltage on the OPDLY and OCDLY pins increases with a constant slope. The slope of the voltage on the two delay pins is controlled by the value of the capacitor connected to each pin. In this case the capacitor on the OCDLY pin is smaller than the capacitor on the OPDLY pin and the voltage on the OCDLY pin ramps much faster than the voltage on the OPDLY pin (both pins are connected to separate 20 µA current sources). The voltages on each delay pin continues to increase with a constant slope until either:

• Either the OPDLY or the OCDLY pin voltages reach a threshold of 3.85 V (if this occurs, the FAULT signal is latched in the low state), or

• The current load of the system falls below 20 A for the OPDLY pin and 40 A for the OCDLY pin

In figure 2 a short circuit fault event is detected at t_{40A_F}. At this time, the FAULT signal transitions to the low state and the GATE pin is pulled to ground. The FAULT state is latched and the chip will pull down the GATE voltage until the EN pin of the ACS760 transitions to the low state and then back to the high state. As shown in the timing diagram, certain ACS760 signals (the FAULT signal and the OCDLY pin voltage) are reset when the EN pin transitions to the low state. These signals are reset in order to guarantee normal device operation (soft start and fault monitoring) when the EN signal transitions back to the high state.
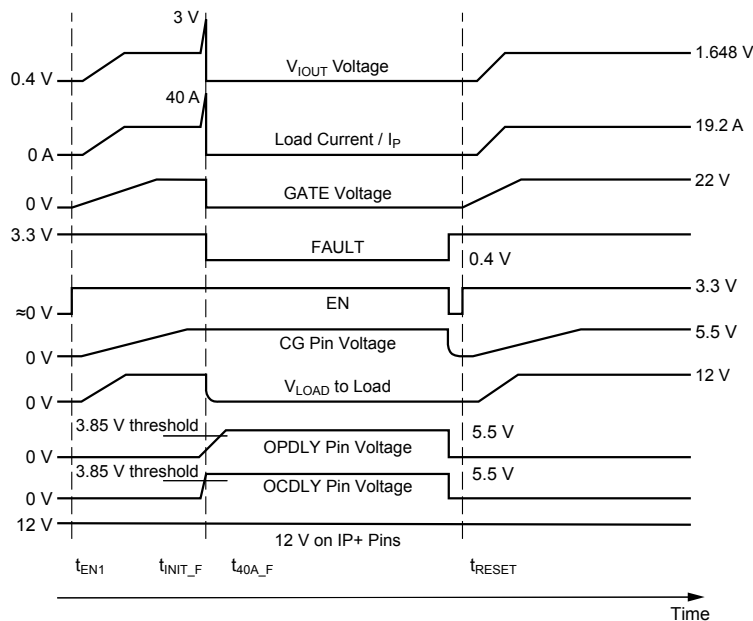

Figure 2. Timing Diagram for 30 to 40 A Load Fault

Hard Short Circuit (50 mΩ from V_{LOAD} to GND) Fault Operation

The timing diagram below specifically shows characteristic operation of the ACS760 when the device is powered on (via the EN pin) and a 50 mΩ short circuit is present from load side of the external MOSFET, S1, to ground.

In figure 3 the system power supply bus reaches the nominal steady state level of 12 V before the EN pin of the ACS760 transitions to the high state at time t_{EN1}. The voltage on the GATE pin increases with a positive slope after the EN pin transitions to the high state. The ramp rate of the GATE pin is controlled by the value of the capacitor connected to the CG pin. In the example shown below a small capacitor is connected to the CG pin and the pin ramps to 5.5 V in < 10 μs.

In panel A of figure 3, the device is enabled into a 50 mΩ short circuit. Therefore, as the GATE voltage increases the current through the external MOSFET increases at a rapid rate. In this example case it is assumed that there is no capacitor on the OCDLY pin. When the current through the MOSFET exceeds the threshold set by the R_{SET} resistor, the voltage on the OCDLY pin rises quickly beginning at t_{40A_F}. As the voltage on the OCDLY pin rises, so does the voltage on the CG pin and the current through the external MOSFET. If there is no capacitor on the OCDLY pin, and if the ACS760 Short Circuit Fault Threshold, I_{SC}, is greater than 100 A, then the OCDLY pin will reach the 3.85 V threshold before the current through the external MOSFET exceeds I_{SC}. This is the case depicted in the panel A. The fault event is detected at t_{GATE_LOW}. At this time, the FAULT signal transitions to the low state and the GATE pin is pulled to ground.

In the event that a large capacitor is connected to the OCDLY pin, the ACS760 will not pull down the gate of the external MOSFET until the current flowing through the MOSFET exceeds I_{SC} (shown in panel B, under the assumption that I_{SC} equals 130 A). The device pulls down the MOSFET GATE approximately 2 μs after the load current exceeds this threshold. If a large capacitor is connected to the OCDLY pin a significant current (> 40 A but < 160 A) may flow through the MOSFET for tens of microseconds before the Short Circuit Fault Threshold trips. These tens of microseconds elapse as the GATE charges and the load current increases, finally exceeding the short circuit threshold.

The FAULT signal is latched and the chip will pull down the GATE voltage until the EN pin of the ACS760 transitions to the low state and then back to the high state. Certain ACS760 signals (soft start and fault monitoring) are reset when the EN pin transitions to the low state. These signals are reset in order to guarantee normal device operation when the EN signal transitions to the high state.
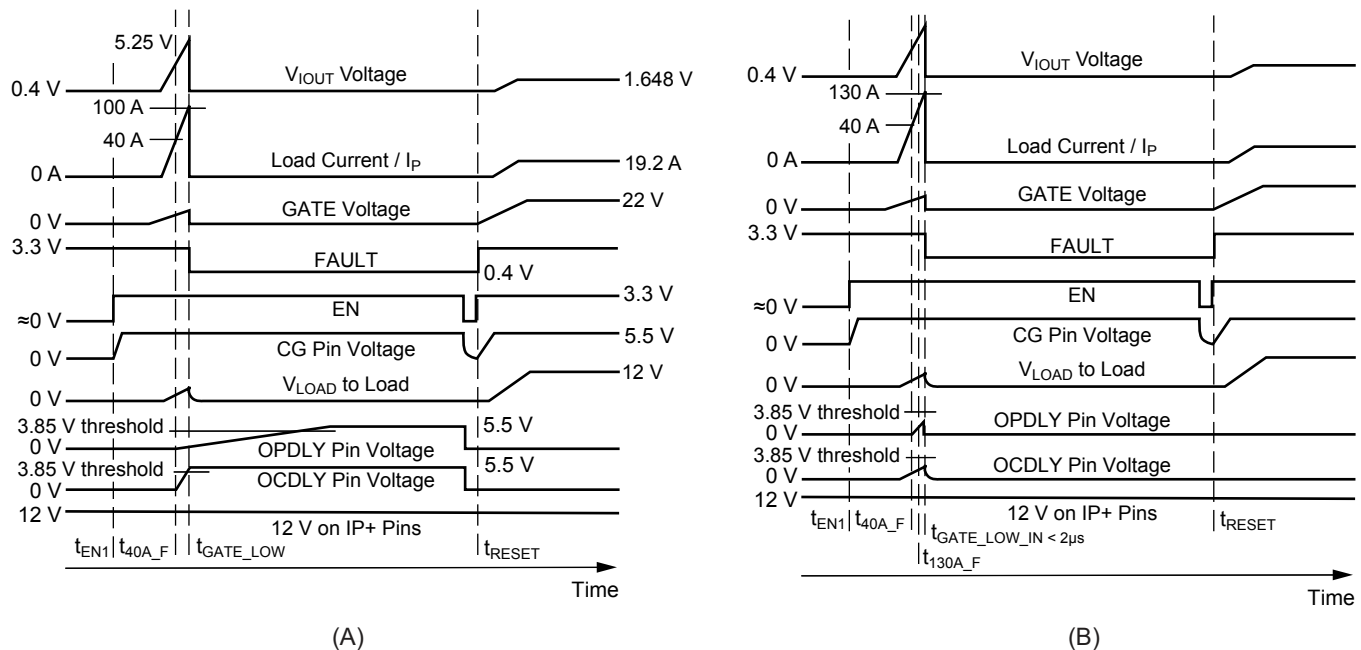

Figure 3. (A) Timing Diagram for a 50 mΩ Short Circuit from V_{LOAD} to GND; (B) Timing Diagram for a 50 mΩ Short Circuit from V_{LOAD} to GND, capacitor C_{OCD} with high rating connected.

S1 Short Fault Operation

The timing diagram in figure 4 shows the characteristic operation of the ACS760 when the power consumed from the 12 V system bus exceeds a 240 V*A or 240 W level. For the operation during a 240 V*A fault condition, refer to figure 1. That section describes the operation of the ACS760 until the time t_{240VA_F}. Figure 4 depicts a 240 V*A fault, but continues on to demonstrate the ability of the ACS760 to detect damage and improper operation of the external MOSFET in an S1 short circuit event.

At t_{240VA_F} the FAULT signal transitions to the low state and the ACS760 pulls down the voltage on the GATE pin. During normal operation, when the GATE pin is at 0 V, the current through the S1 MOSFET (and therefore through the ACS760) equals approximately 0 A. However, in the case depicted in figure 4, current through the S1 MOSFET flows even though the GATE pin is pulled low. If a FAULT has occurred and more than 2.1 A flow through the ACS760, then the S1SHORT signal transitions to the low state. When the S1SHORT signal is low, that indicates to the system that the ACS760 cannot turn off the external MOSFET (for example, when a short circuit exists between the source and the drain of the MOSFET). In the case depicted, the system shuts down the 12 V power supply after the S1SHORT signal transitions to the low state.

Note that, in some cases, the GATE of the S1 MOSFET may be shorted to the source or drain of the MOSFET. In this case the ACS760 may not be able to pull down the gate of the S1 MOS-FET. However, in this case the ACS760 will still register an S1 Short even if the gate potential is equal to or greater than 12 V.

If the ACS760 is disabled (EN pin in the low state) and greater than 2.1 A flows through the ACS760, then the device will register an S1 Short condition and the S1SHORT pin will transition to the low state. The voltage on the GATE pin is not used as a determining factor when sensing an S1 Short condition.

The S1SHORT signal will not reset to a high state until power to the device is cycled. Toggling the EN pin does not reset the latched S1 Short state.

Determining the Root Cause of an ACS760 Fault Event

The following truth table provides system debugging information in the event of a fault event during use of the ACS760. Note that for all of the fault conditions listed, it is possible to monitor the voltages of various ACS760 output pins and determine the cause of the ACS760 FAULT event.
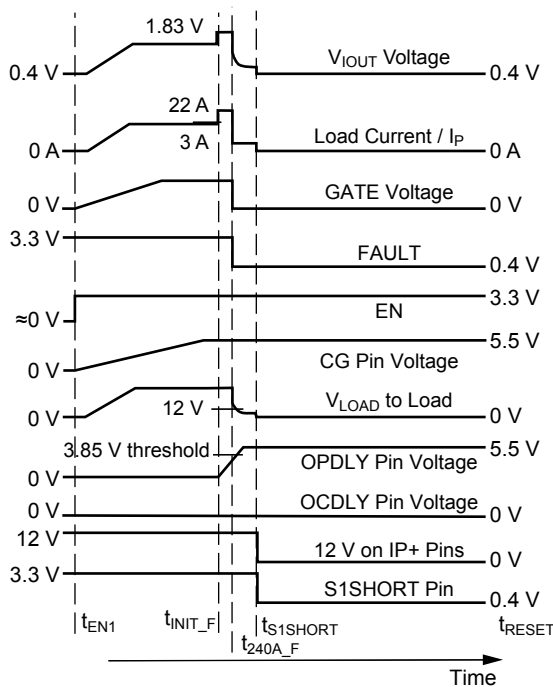

Figure 4. Timing Diagram for S1 Short

Fault Condition Truth Table

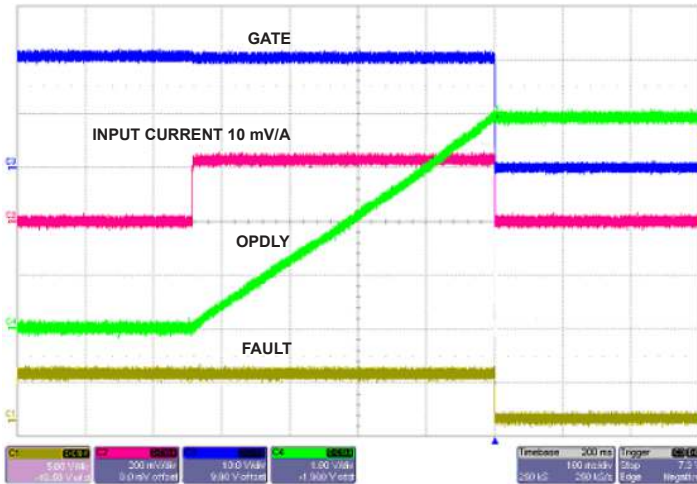| Pin Logic State			Probable Root Cause
FAULT Pin	**OPDLY Pin**	**OCDLY Pin**	
Low	High	Low	240 V*A system power level, $P_{F(th)}$, exceeded
Low	Don't Care	High	I_P Fault Current Threshold, I_{PF}, exceeded
Low	Low	Low	Short Circuit Fault Threshold, I_{SC}, exceeded

Fault Condition Characteristics

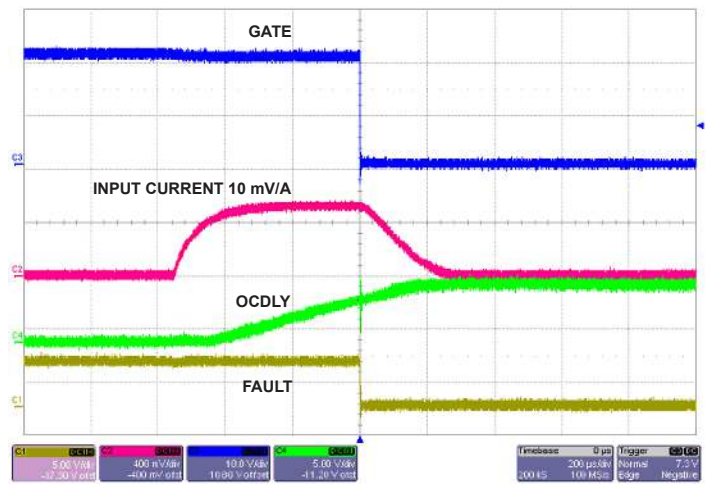Figure 5. 240 V*A fault: with V_{CC} = 12 V and ACS760 enabled, apply load

Figure 6. I_{PF} event: with V_{CC} = 12 V and ACS760 enabled, apply load

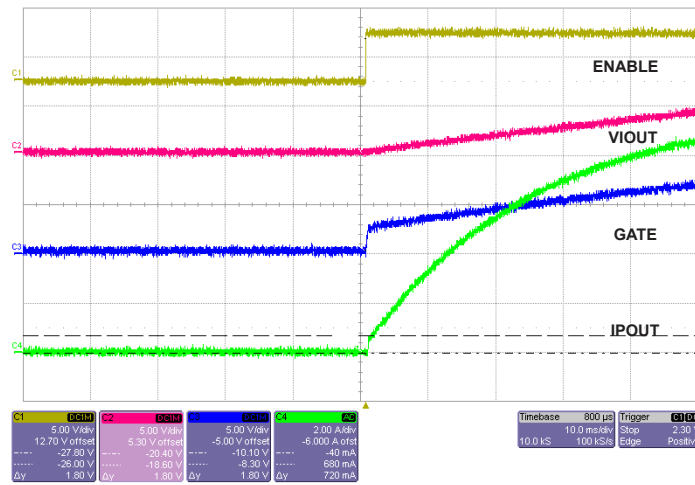Figure 7. Hot-swap with 1 µF capacitor from CG pin to GND, resistive load approximately 0.17 Ω. capacitive load approximately 3300 µF; C_G capacitor limits inrush current to 720 mA during hot swap event (15 A current probe used)
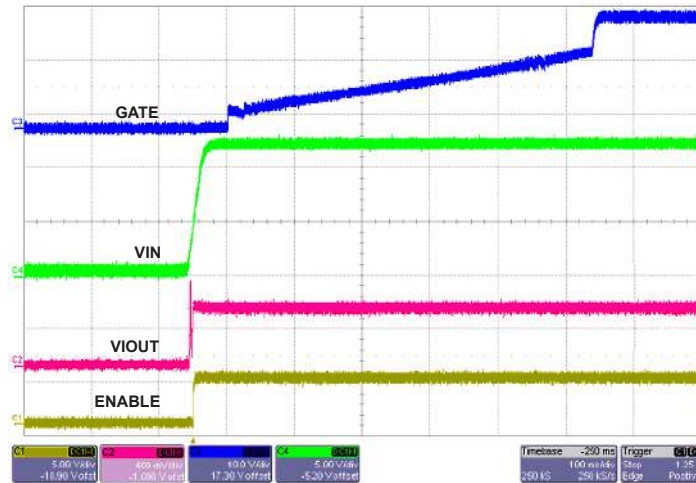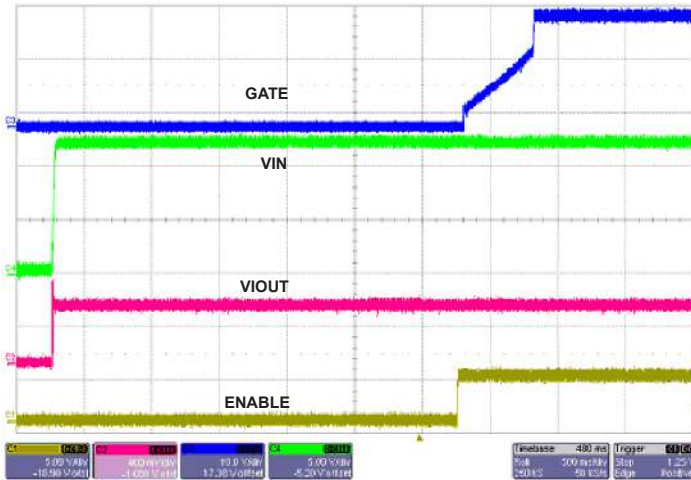
Figure 8. Power-up: with the enable jumper on, apply V_{CC}

Figure 9. Power-up: with V_{CC} on, apply the enable jumper (enables ACS760)
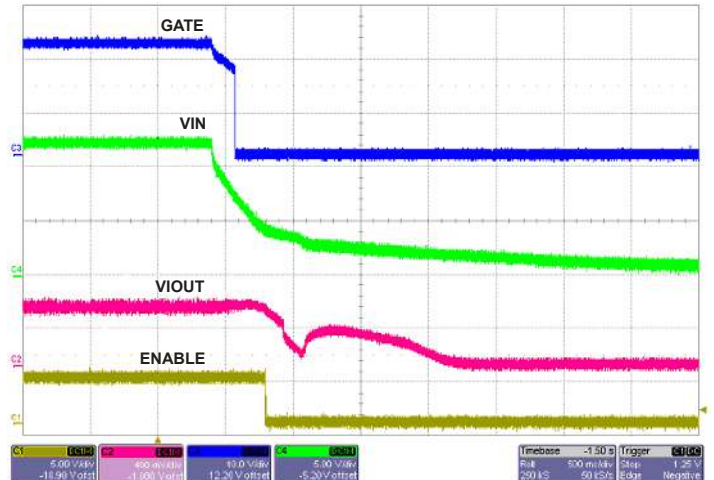
Figure 10. Power-down: with enable jumper on, remove supply (disables ACS760)
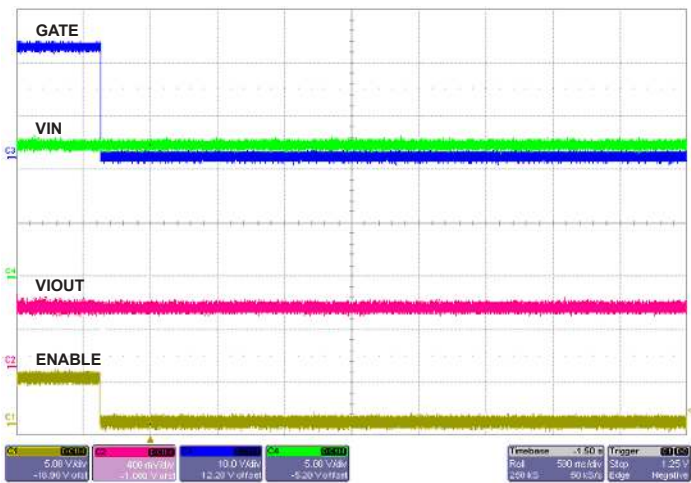
Figure 11. Power-up to power-down (a): remove enable jumper (disables ACS760, but V_{CC} and V_{IOUT} stay high (see figure 12)
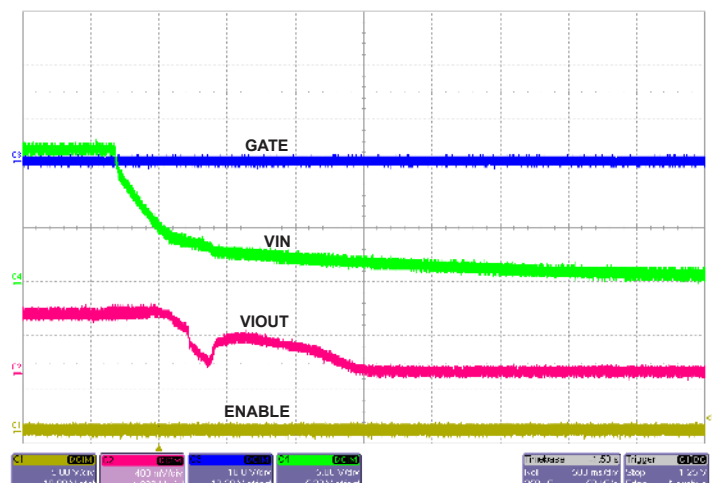

Figure 12. Power-up to power-down (b): with ACS760 disabled (see figure 11), remove supply (V_{CC} and V_{IOUT} brought low)

Application Information

Current Mode Operation

The ACS760 has the ability to operate in pure Current Mode. If the Allegro ACS760 detects power in excess of 240 V*A, the FAULT output of the device transitions from a logic high to a logic low level and the integrated gate driver circuitry pulls the gate of an external MOSFET to GND. The delay between the detection of an excess power condition and gate shutdown is set by an external capacitor on the OPDLY pin to GND. The ACS760, however, has the ability to override the Power Mode fault condition to operate in pure Current Mode.

Pulling the OPDLY pin to GND, disables the 240 V*A power fault to allow the ACS760 to operate in pure Current Mode. The user may then set the current fault threshold by adjusting the resistor value from the ISET pin to GND. If the current exceeds the set threshold, the FAULT output of the device trips and the gate of the external MOSFET is pulled to GND. The delay between the detection of a soft short circuit condition and gate shutdown is set by the capacitor on the OCDLY pin. In Current Mode Operation, the ACS760 has the ability to detect a S1 Short and Hard Short.

Filtering

In applications where the FAULT and S1SHORT pins are pulled-up prior to providing power to the device, be sure to add an RC filter with the pull-up resistor closest to the FAULT and S1SHORT pins. This will ensure that the ACS760 S1 Short and Fault logic levels remain proper under this application condition. See diagram below.
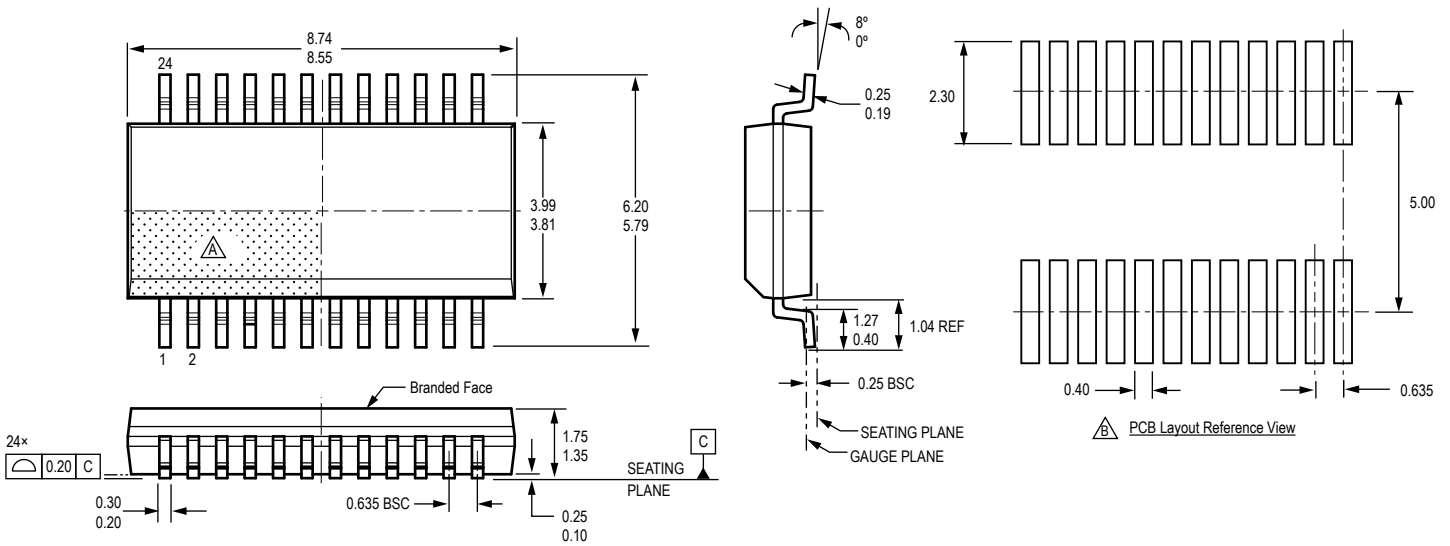

Ⓐ RV1 is required only for inductive loads.
Ⓑ D1 should be a Schottky for inductive loads, to eliminate over-stress of the ACS760.
Ⓒ FB– is tied to GND at the point of load.
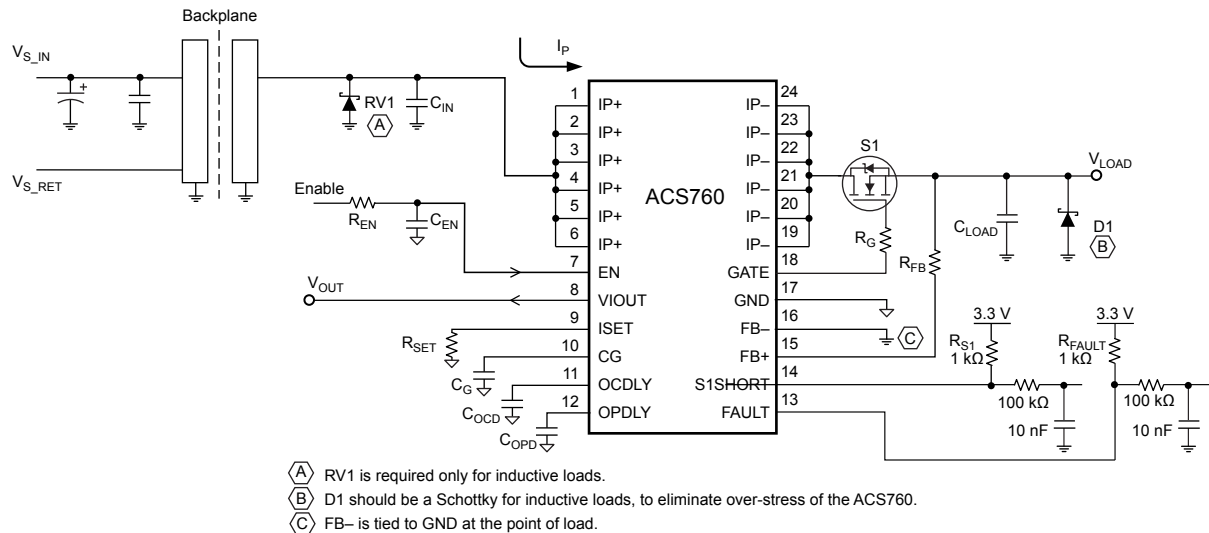
Package LF, 24-pin QSOP

**For Reference Only – Not for Tooling Use**
(Reference Allegro DWG-0000387, Rev. 2 and JEDEC MO-137 AE)
Dimensions in millimeters
Dimensions exclusive of mold flash, gate burrs, and dambar protrusions
Exact case and lead configuration at supplier discretion within limits shown

8.74
8.55

24

3.99
3.81

6.20
5.79

Ⓐ

1 2

8º
0º

0.25
0.19

2.30

5.00

1.27
0.40   1.04 REF

0.25 BSC

0.40   0.635

Ⓑ PCB Layout Reference View

Branded Face

24×

⌒ 0.20 C

1.75
1.35

0.30
0.20

0.635 BSC

SEATING
PLANE

C

0.25
0.10

SEATING PLANE
GAUGE PLANE

XXXXXXX
XLF-XXX
Lot Number

Ⓐ Terminal #1 mark area

Ⓑ Reference pad layout (reference IPC7351 SOP63P600X175-24M)
All pads a minimum of 0.20 mm from all adjacent pads; adjust as necessary
to meet application process requirements and PCB layout tolerances

Ⓒ Branding scale and appearance at supplier discretion
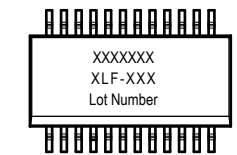
Ⓒ Standard Branding Reference View

Line 1: Part Number
Line 2: Temp Code, Package Code - Amps
Line 3: Assembly Lot Number

ALLEGRO
microsystems

Revision History

Number	Date	Description
9	May 18, 2020	Minor editorial updates
10	July 14, 2022	Updated part status to Discontinued; updated package drawing (page 15)

The products described herein are manufactured under one or more of the following U.S. patents: 5,619,137; 5,621,319; 6,781,359; 7,075,287; 7,166,807; 7,265,531; 7,425,821; or other patents pending.

For the latest version of this document, visit our website:

www.allegromicro.com